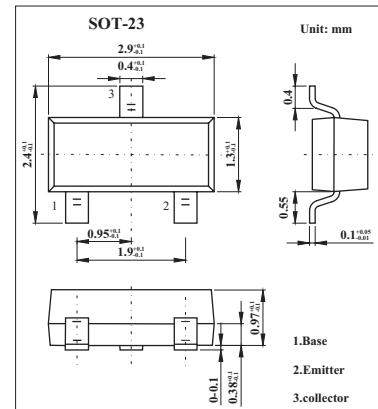


NPN Epitaxial Planar Silicon Transistor

2SC4852

■ Features

- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	25	V
Collector-emitter voltage	V _{CEO}	15	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector current (pulse)	I _{CP}	200	mA
Base current	I _B	20	mA
Collector dissipation	P _C	250	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 15V, I _E =0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 4V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} = 2V , I _C = 5mA	800	3200		
Gain bandwidth product	f _T	V _{CE} = 5V , I _C = 10mA		240		MHz
Output capacitance	C _{ob}	V _{CB} = 10V , f = 1.0MHz		1.4		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA , I _B = 1mA		14	30	mV
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 10mV , I _B = 1mA		0.74	1.1	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA , I _E = 0	25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA , R _{BE} = ∞	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _C = 0	5			V
On resistance	R _{on}	I _B = 3mA, f = 1.0MHz		0.9		Ω

■ Marking

Marking	YT
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